March 2014



FGL60N100BNTD 1000 V, 60 A NPT Trench IGBT

Features

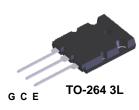
- · High Speed Switching
- Low Saturation Voltage: V_{CE(sat)} = 2.5 V @ I_C = 60 A
- High Input Impedance
- Built-in Fast Recovery Diode

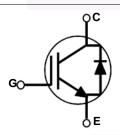
Applications

· UPS, Welder



Using Fairchild's proprietary trench design and advanced NPT technology, the 1000V NPT IGBT offers superior conduction and switching performances, high avalanche ruggedness and easy parallel operation. This device offers the optimum performance for hard switching application such as UPS, welder applications.





Absolute Maximum Ratings

Symbol	Description		Ratings	Unit
V _{CES}	Collector to Emitter Voltage		1000	V
V _{GES}	Gate to Emitter Voltage		± 25	V
	Collector Current	@ T _C = 25°C	60	А
I _C Collecto	Collector Current	@ T _C = 100 ^o C	42	A
I _{CM (1)}	Pulsed Collector Current	@ T _C = 25°C	200	A
I _F	Diode Continuous Forward Current	@ T _C = 100 ^o C	15	A
P _D	Maximum Power Dissipation	@ T _C = 25°C	180	W
	Maximum Power Dissipation	@ T _C = 100°C	72	W
TJ	Operating Junction Temperature	-55 to +150	°C	
T _{stg}	Storage Temperature Range	-55 to +150	°C	
TL	Maximum Lead Temp. for soldering Purposes, 1/8" from case for 5 second	300	°C	

Notes: 1: Repetitive rating: Pulse width limited by max. junction temperature

Thermal Characteristics

Symbol	Parameter	Ratings	Unit
R _{0JC} (IGBT) Thermal Resistance, Junction to Case		0.69	°C/W
R _{0JC} (Diode) Thermal Resistance, Junction to Case		2.08	°C/W
R _{0JA} Thermal Resistance, Junction to Ambient		25	°C/W

· ·		Top Mark	Packag	ge Packing Method		Re	el Size	Tape Width		Quantity	
		TO-264	54 Tube			N/A	N/A		30		
Electric	al Cha	aracteristics o	f the IG	BB.	T _C = 25°C unless otherwise	noted					
Symbol		Parameter			Test Conditions		Min.	Тур.	Max	. Unit	
Off Charac	teristics						-				
BV _{CES}	Collecto	r to Emitter Breakdow	n Voltage	V _{GE}	= 0 V, I _C = 1 mA		1000	-	-	V	
I _{CES}	Collecto	r Cut-Off Current		$V_{CE} = V_{CES}, V_{GE} = 0 V$		-	-	1	mA		
I _{GES}	G-E Lea	akage Current		V _{GE}	$_{\rm E}$ = V _{GES} , V _{CE} = 0 V		-	-	±500	nA	
On Charac	teristics										
V _{GE(th)}	G-E Threshold Voltage		I _C = 60 mA, V _{CE} = V _{GE}		4.0	5.0	7.0	V			
			I _C =10 A, V _{GE} = 15 V		-	1.5	1.8	V			
V _{CE(sat)}	Collector to Emitter Saturation Voltage		I _C = 60 A, V _{GE} = 15 V,		-	2.5	2.9	V			
Dynamic C	haracter	istics						_+	+		
C _{ies}	Input Capacitance Output Capacitance		V _{CE} = 10 V, V _{GE} = 0 V, f = 1MHz		- 1	6000	-	pF			
C _{oes}					-	260	-	pF			
C _{res}	Reverse	e Transfer Capacitance	ice				-	200	-	pF	
Switching	Characte	ristics									
t _{d(on)}	Turn-On	Delay Time					-	140	-	ns	
r	Rise Tin	ne		$V_{CC} = 600 \text{ V}, \text{ I}_{C} = 60 \text{ A},$ $R_{G} = 51 \Omega, \text{ V}_{GE} = 15 \text{ V},$ Inductive Load, T _C = 25°C			-	320	-	ns	
t _{d(off)}	Turn-Of	f Delay Time				-	630	-	ns		
ŀf	Fall Tim	e					-	130	-	ns	
Qg	Total Ga	ate Charge		. ,			-	275	-	nC	
Q _{ge}	Gate to	Emitter Charge			= 600 V, I _C = 60 A, = 15 V, T _C = 25°C		-	45	-	nC	
Q _{gc}	Gate to	Collector Charge		$\sim _{\rm GE} = 15$ v, $1_{\rm C} = 25$ C			-	95	-	nC	

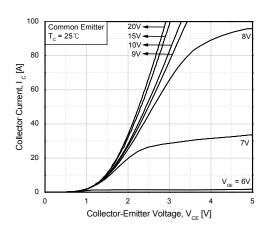
Electrical Characteristics of the Diode T_C = 25°C unless otherwise noted

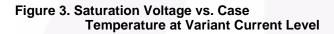
Symbol	Parameter	Test Conditions	Min.	Тур.	Max	Unit
V _{FM}	Diode Forward Voltage	I _F = 15 A	-	1.2	1.7	V
		I _F = 60 A	-	1.8	2.1	V
t _{rr}	Diode Reverse Recovery Time	I _F = 60 A, di/dt = 20 A/us	-	1.2	1.5	us
I _R	Instantaneous	V _{RRM} = 1000 V	-	0.05	2.0	uA

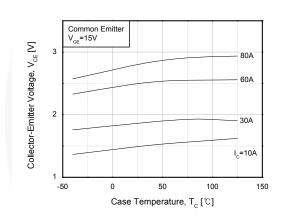
FGL60N100BNTD — 1000 V, 60 A NPT Trench IGBT

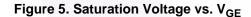
Typical Performance Characteristics

Figure 1. Typical Output Characteristics









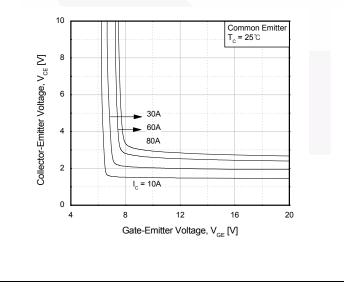
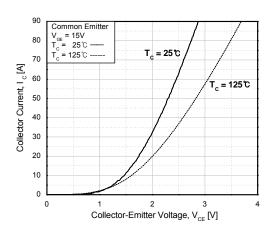


Figure 2. Typical Saturation Voltage Characteristics





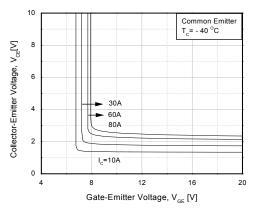
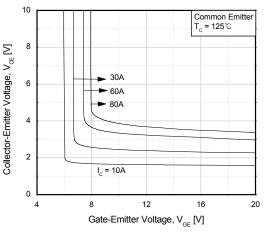


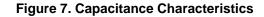
Figure 6. Saturation Voltage vs. V_{GE}

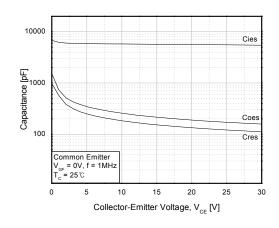


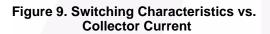
©2000 Fairchild Semiconductor Corporation FGL60N100BNTD Rev. C2

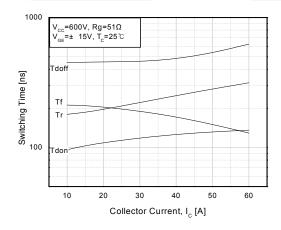
FGL60N100BNTD — 1000 V, 60 A NPT Trench IGBT

Typical Performance Characteristics











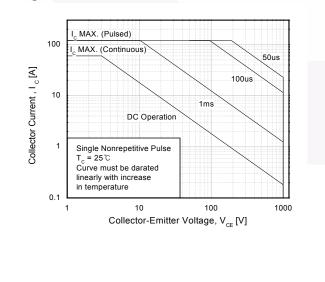


Figure 8. Switching Loss vs. Gate Resistance

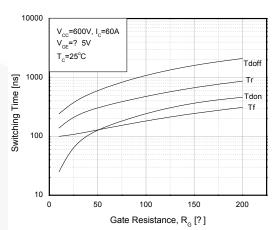
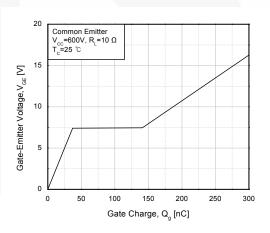
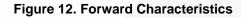
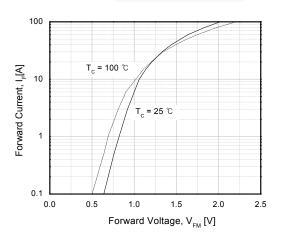
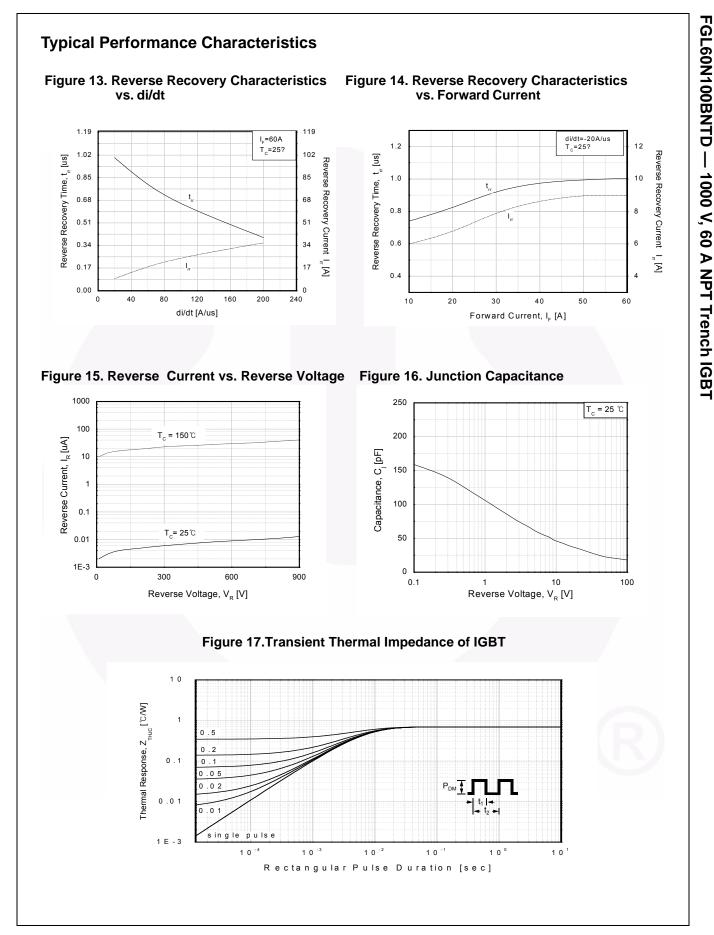


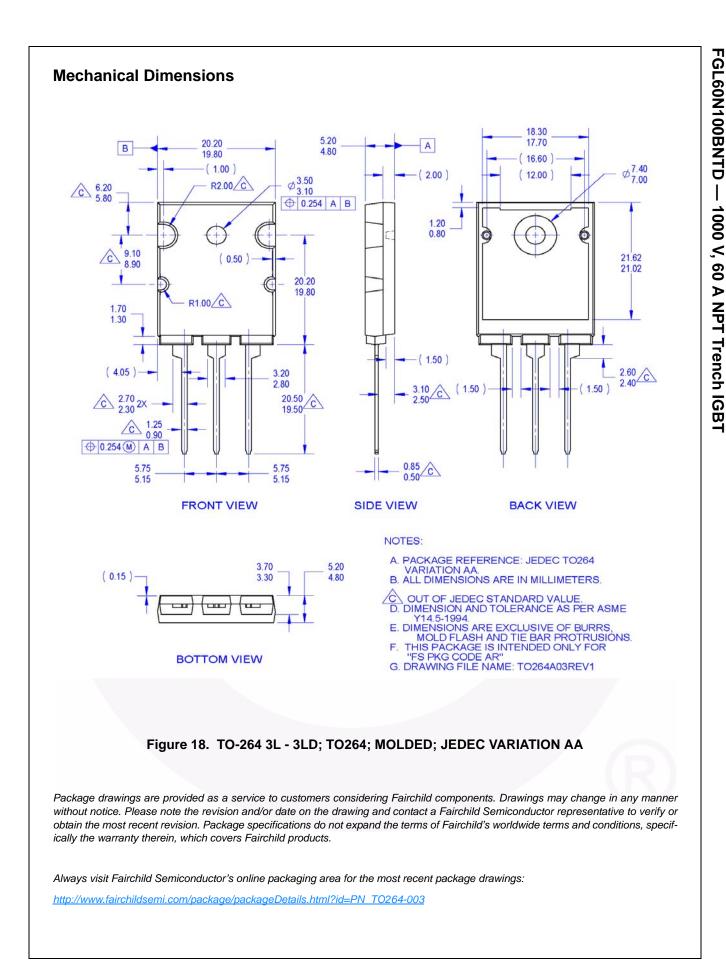
Figure 10. Gate Charge Characteristics













SEMICONDUCTOR

TRADEMARKS

The following includes registered and unregistered trademarks and service marks, owned by Fairchild Semiconductor and/or its global subsidiaries, and is not intended to be an exhaustive list of all such trademarks.

®

AccuPower™ AX-CAF BitSiC™ Build it Now™ CorePLUS™ CorePOWER™ CROSSVOLT™ CTL™ Current Transfer Logic™ **DEUXPEED[®]** Dual Cool™ EcoSPARK[®] EfficentMax™ ESBC™

Fairchild® Fairchild Semiconductor® FACT Quiet Series™ FAST® FastvCore™ FETBench™

FRFET® Global Power ResourceSM GreenBridge™ Green FPS™ Green FPS™ e-Series™ G*max*™ GTO™ IntelliMAX™ **ISOPLANAR™** Marking Small Speakers Sound Louder and Better™ MegaBuck™ MICROCOUPLER™ MicroFET™ MicroPak™ MicroPak2™ MillerDrive™ MotionMax™ mWSaver[®] OptoHiT™ **OPTOLOGIC[®] OPTOPLANAR[®]**

F-PFS™

PowerTrench[®] PowerXS™ Programmable Active Droop™ QFĔT[®] QS™ Quiet Series™ RapidConfigure™ тΜ Saving our world, 1mW/W/kW at a time™ SignalWise™ SmartMax™ SMART START™ Solutions for Your Success™ SPM[®] STEALTH™ SuperFET[®] SuperSOT™-3 SuperSOT™-6 SuperSOT™-8 SupreMOS® SyncFET™

Sync-Lock™ **GENERAL** ^{®'} TinyBoost TinyBuck® TinyCalc™ TinyLogic® TINYOPTO™ TinyPower™ TinyPWM™ TinyWire™ TranSiC™ TriFault Detect™ TRUECURRENT®* µSerDes™ μ_{Ser} UHC® Ultra FRFET™

UniFET™ VCX™ VisualMax™ VoltagePlus™ XS™

*Trademarks of System General Corporation, used under license by Fairchild Semiconductor.

DISCLAIMER

R

FACT®

FPS™

FAIRCHILD SEMICONDUCTOR RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION, OR DESIGN. FAIRCHILD DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS. THESE SPECIFICATIONS DO NOT EXPAND THE TERMS OF FAIRCHILD'S WORLDWIDE TERMS AND CONDITIONS, SPECIFICALLY THE WARRANTY THEREIN, WHICH COVERS THESE PRODUCTS.

LIFE SUPPORT POLICY FAIRCHILD'S PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE EXPRESS WRITTEN APPROVAL OF FAIRCHILD SEMICONDUCTOR CORPORATION.

As used here in:

- Life support devices or systems are devices or systems which, (a) are 1. intended for surgical implant into the body or (b) support or sustain life, and (c) whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in a significant injury of the user.
- A critical component in any component of a life support, device, or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness

ANTI-COUNTERFEITING POLICY

Fairchild Semiconductor Corporation's Anti-Counterfeiting Policy. Fairchild's Anti-Counterfeiting Policy is also stated on our external website, www.Fairchildsemi.com, under Sales Support.

Counterfeiting of semiconductor parts is a growing problem in the industry. All manufactures of semiconductor products are experiencing counterfeiting of their parts. Customers who inadvertently purchase counterfeit parts experience many problems such as loss of brand reputation, substandard performance, failed application, and increased cost of production and manufacturing delays. Fairchild is taking strong measures to protect ourselves and our customers from the proliferation of counterfeit parts. Fairchild strongly encourages customers to purchase Fairchild parts either directly from Fairchild or from Authorized Fairchild Distributors who are listed by country on our web page cited above. Products customers buy either from Fairchild directly or from Authorized Fairchild Distributors are genuine parts, have full traceability, meet Fairchild's quality standards for handing and storage and provide access to Fairchild's full range of up-to-date technical and product information. Fairchild and our Authorized Distributors will stand behind all warranties and will appropriately address and warranty issues that may arise. Fairchild will not provide any warranty coverage or other assistance for parts bought from Unauthorized Sources. Fairchild is committed to combat this global problem and encourage our customers to do their part in stopping this practice by buying direct or from authorized distributors.

PRODUCT STATUS DEFINITIONS Definition of Terms

Datasheet Identification	Product Status	Definition
Advance Information	Formative / In Design	Datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary First Production		Datasheet contains preliminary data; supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve design.
No Identification Needed	Full Production	Datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve the design.
Obsolete	Not In Production	Datasheet contains specifications on a product that is discontinued by Fairchild Semiconductor. The datasheet is for reference information only.

ON Semiconductor and are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at <u>www.onsemi.com/site/pdf/Patent-Marking.pdf</u>. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor has against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death ass

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor 19521 E. 32nd Pkwy, Aurora, Colorado 80011 USA Phone: 303-675-2175 or 800-344-3860 Toll Free USA/Canada Fax: 303-675-2176 or 800-344-3867 Toll Free USA/Canada Email: orderlit@onsemi.com N. American Technical Support: 800–282–9855 Toll Free USA/Canada Europe, Middle East and Africa Technical Support: Phone: 421 33 790 2910

Japan Customer Focus Center Phone: 81-3-5817-1050 ON Semiconductor Website: www.onsemi.com

Order Literature: http://www.onsemi.com/orderlit

For additional information, please contact your local Sales Representative

© Semiconductor Components Industries, LLC